

Remarks

Claims 78-90 have been cancelled and new claims 91-103 have been added, leaving claims 91-103 pending in the present application. The new claims are supported by the originally-filed application by exemplary embodiments of the invention described at, for example, Figs. 1-8 and pages 4-8. Applicant requests consideration of these new claims.

Claims 91-103 are allowable for at least the reason they recite features that are not taught or suggested by the cited references. For example, claim 91 recites methods for forming a plurality of floating gate transistors that includes forming a first layer against and physically contacting an oxide-comprising layer with the first layer including dopant that physically contacts the oxide-comprising layer. Claim 91 further recites forming a second layer against and physically contacting the first layer with the second layer including substantially undoped semiconductive material. For at least the reason claim 91 recites substantially undoped semiconductive material against and physically contacting a first layer including semiconductive material and a dopant with the dopant of the first layer physically contacting an oxide-comprising layer, claim 91 is allowable. Further, the cited references do not teach or suggest forming floating gates that include the recited first and second layers and forming an oxide layer over the floating gates and source and drain regions proximate the floating gates as recited in claim 91.

Pending claims 91-103 are believed to be in immediate condition for allowance. Applicant requests allowance of claim 91-103 in the Examiner's next action. If the Examiner's next action is anticipated to be anything other than a Notice of Allowance, the undersigned respectfully requests a telephone interview prior to issuance of any such subsequent action.

Respectfully submitted,

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By: 

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